

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

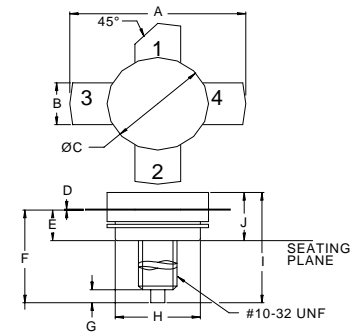
The **ASI MRF450A** is Designed for 12.5 Volt Power Amplifier Applications up to 30 MHz.

FEATURES INCLUDE:

- $P_{OUT} = 50\text{ W}$
- $P_G = 11\text{ dB Min. @ } 30\text{MHz \& } 50\text{W}$
- Efficiency 50%

MAXIMUM RATINGS

I_C	7.5 A
V_{CBO}	40 V
V_{CEO}	20 V
V_{EBO}	4.0 V
P_{DISS}	115 W @ $T_C = 25\text{ }^\circ\text{C}$
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	1.53 °C/W

PACKAGE STYLE .500" 4L STUD


DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	1.010 / 25.65	1.050 / 26.67
B	.220 / 5.59	.230 / 5.84
C	.495 / 12.57	.505 / 12.83
D	.003 / 0.08	.007 / 0.18
E	.160 / 4.06	.180 / 4.57
F	.622 / 15.80	
G	.100 / 2.54	.130 / 3.31
H	.415 / 10.54	.425 / 10.80
I	.720 / 18.29	
J	.250 / 6.35	.290 / 7.37

1 = COLLECTOR 2 = BASE 3 & 4 = EMITTER

CHARACTERISTICS $T_C = 25\text{ }^\circ\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CES}	$I_C = 20\text{ mA}$	40			V
BV_{CEO}	$I_C = 100\text{ mA}$	20			V
BV_{CBO}	$I_C = 20\text{ mA}$	40			V
BV_{EBO}	$I_E = 10\text{ mA}$	4.0			V
h_{FE}	$V_{CE} = 5.0\text{ V}$ $I_C = 1.0\text{ A}$	10			---
C_{OB}	$V_{CB} = 15\text{ V}$ $f = 1.0\text{ MHz}$			200	pF
G_{PE}	$V_{CC} = 13.6$ $P_{OUT} = 50\text{ W}$ $f = 30\text{ MHz}$	11	15		dB
η_C		50			%